



A cross-sectional view of a substrate assembly 300. The assembly consists of a top layer 302 with diagonal hatching, a middle layer 300, and a bottom layer 304.

FIG. 5B is a cross-sectional view of a substrate 5B. The substrate 5B is a rectangular block with a central layer 304 and two side layers 306 and 310. The central layer 304 has a central opening 308 and two side openings 312. The side layers 306 and 310 are positioned on the left and right sides of the central layer 304, respectively. The substrate 5B is shown with a hatched pattern.

A cross-sectional view of a multi-layered structure 5C. The structure consists of several layers and internal features. From top to bottom, the layers are labeled 326, 324, 306, 324, 310, 324, and 326. Two hatched layers are labeled 316 and 318. Internal features include a central rectangular cavity 308 and side features 312 and 314. A reference arrow 5C points to the top layer.

A cross-sectional view of a semiconductor device. A central channel region, labeled 320, is defined by a top layer 310 and a bottom layer 324. The channel is flanked by side regions 314 and 316. The side regions 314 and 316 are further divided into sub-regions 318 and 306. The bottom layer 324 is also divided into sub-regions 326 and 304. Arrows indicate a flow or direction of movement from the side regions towards the central channel.

FIG. 5C

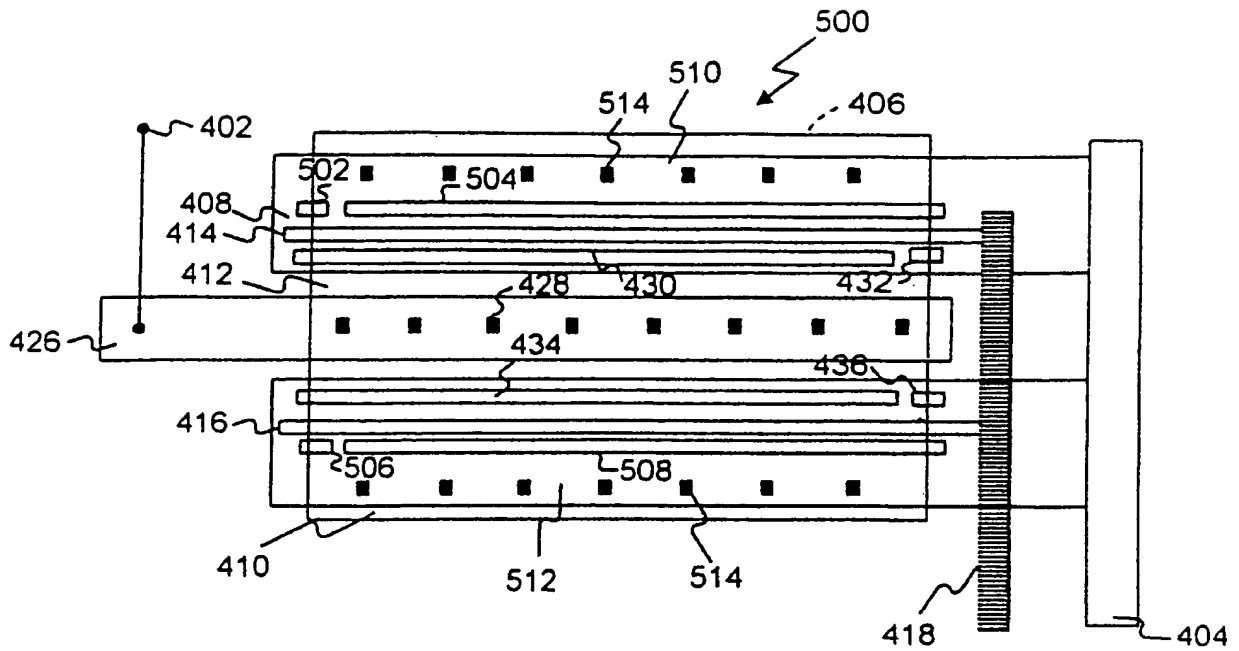


FIG. 7

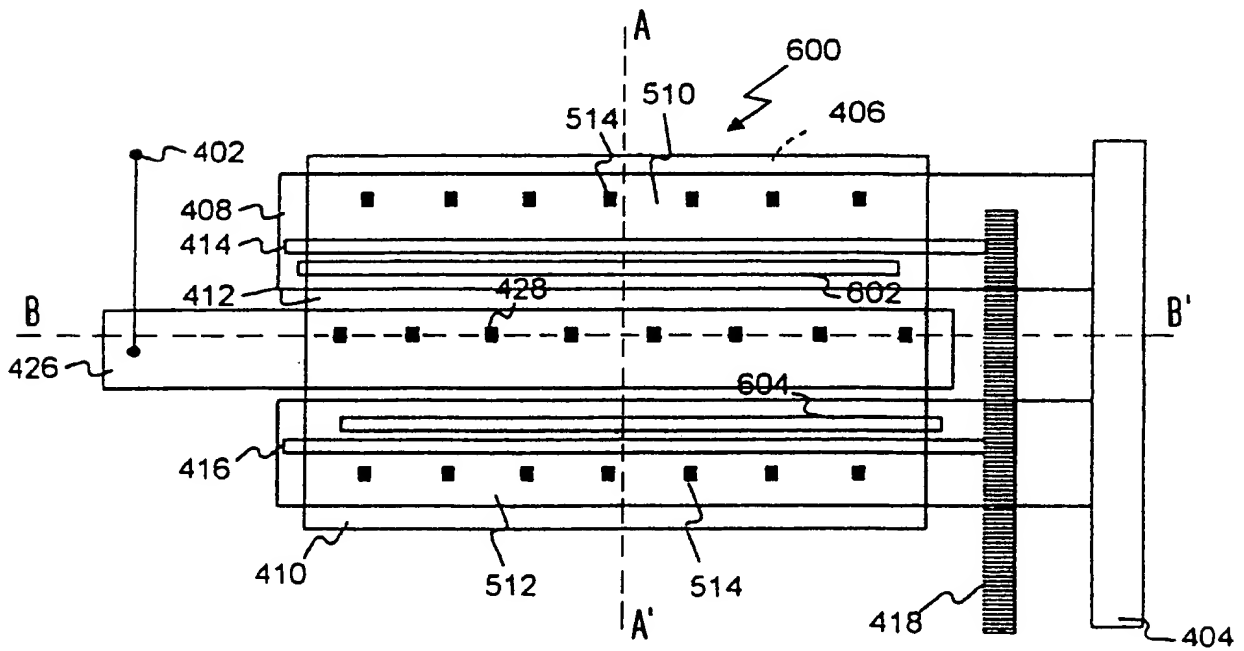


FIG. 8